



Bipolar NPN Bare Die – BTN6017

Part Description

The BTN6017 is a silicon BJT transistor available in bare die form and well suited for use in general purpose switching and amplifier applications.

Key Parameters:

- VCBO = 200V
- VCEO = 170V
- VEBO = 6V
- hFE = 40- @ VCE = 5V, IC = 2A
- VCE(Sat) = 1V @ IC = 5A, IB = 500mA
- fT = 90 MHz @ VCE = 10V, IE = 0A
- COBO = 80pF @ VCB = 50V

Features

Low VCE(sat). Designed to provide performance equivalent to BUY48

Die Size (Unawn)

2100µm X 2100µm, 83 Mils X 83 Mils

This is a shortform datasheet only

For the full datasheet

Please contact sales@siliconsupplies.com

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